TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

# TC7MA2374FK

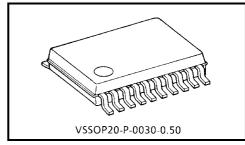
Low-Voltage Octal D-Type Flip-Flop with 3.6 V Tolerant Inputs and Outputs

The TC7MA2374FK is a high performance CMOS octal D-type flip-flop. Designed for use in 1.8 V, 2.5 V or 3.3 V systems, it achieves high speed operation while maintaining the CMOS low power dissipation.

It is also designed with over voltage tolerant inputs and outputs up to  $3.6\ V$ .

This 8 bit D-type flip-flop is controlled by a clock input (CK) and output enable input  $(\overline{OE})$ . When the  $\overline{OE}$  input is high, the eight outputs are in a high impedance state.

The 26  $\Omega$  series resistor helps reducing output overshoot and undershoot without external resistor.



Weight: 0.03 g (typ.)

All inputs are equipped with protection circuits against static discharge.

#### **Features**

- 26 Ω series resistors on outputs.
- Low voltage operation:  $VCC = 1.8 \sim 3.6 \text{ V}$
- High speed operation:  $t_{pd} = 5.1 \text{ ns (max) (VCC} = 3.0 \sim 3.6 \text{ V)}$

 $t_{pd} = 6.2 \text{ ns (max)} (V_{CC} = 2.3 \sim 2.7 \text{ V})$ 

 $t_{pd} = 9.8 \text{ ns (max) (V}_{CC} = 1.8 \text{ V})$ 

- 3.6 V tolerant inputs and outputs.
- Output current:  $I_{OH}/I_{OL} = \pm 12 \text{ mA (min)} (V_{CC} = 3.0 \text{ V})$

 $I_{OH}/I_{OL} = \pm 8 \text{ mA (min)} (V_{CC} = 2.3 \text{ V})$ 

 $IOH/IOL = \pm 4 \text{ mA (min) (VCC} = 1.8 \text{ V)}$ 

- Latch-up performance: ±300 mA
- ESD performance: Machine model > ±200 V

Human body model  $> \pm 2000 \text{ V}$ 

- Package: VSSOP (US20)
- Power down protection is provided on all inputs and outputs.
- Supports live insertion/withdrawal (\*)
  - \*: To ensure the high-impedance state during power up or power down,  $\overline{OE}$  should be tied to  $V_{CC}$  through a pullup resistor; the minimum value of the resistor is determined by the current-sourcing capability of the driver.

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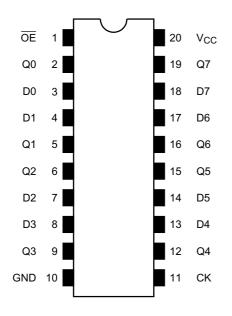
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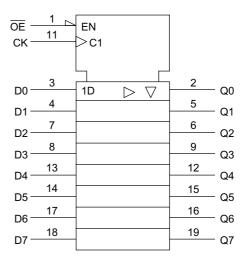
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# Pin Assignment (top view)



### **IEC Logic Level**



#### **Truth Table**

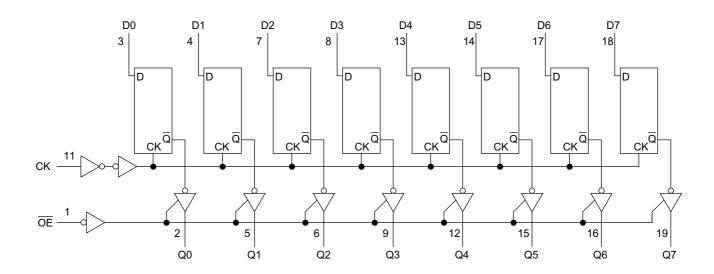
	Intputs	Outputs	
ŌĒ	CK	D	Outputs
Н	Х	Х	Z
L	$\rightarrow$	Х	Q <sub>n</sub>
L		L	L
L		Н	Н

X: Don't care

Z: High impedance

Q<sub>n</sub>: No change

### **System Diagram**





### **Maximum Ratings**

Characteristics	Symbol	Rating	Unit	
Power supply voltage	V <sub>CC</sub>	-0.5~4.6	V	
DC input voltage	V <sub>IN</sub>	-0.5~4.6	V	
DC output voltage	Vour	-0.5~4.6 (Note1)	V	
DC output voltage	Vout	-0.5~V <sub>CC</sub> + 0.5 (Note2)	V	
Input diode current	I <sub>IK</sub>	-50	mA	
Output diode current	lok	±50 (Note3)	mA	
DC output current	lout	±50	mA	
Power dissipation	PD	180	mW	
DC V <sub>CC</sub> /ground current	I <sub>CC</sub> /I <sub>GND</sub>	±100	mA	
Storage temperature	T <sub>stg</sub>	-65~150	°C	

Note1: Off-state

Note2: High or low state. IOUT absolute maximum rating must be observed.

Note3:  $V_{OUT} < GND, V_{OUT} > V_{CC}$ 

### **Recommended Operating Range**

Characteristics	Symbol	Rating	Unit	
Supply voltage	V	1.8~3.6		
Supply voltage	V <sub>CC</sub>	1.2~3.6 (Note4)	V	
Input voltage	V <sub>IN</sub>	-0.3~3.6	V	
Output voltage	\/	0~3.6 (Note5)	V	
Output voltage	Vout	0~V <sub>CC</sub> (Note6)		
		±12 (Note7)		
Output current	I <sub>OH</sub> /I <sub>OL</sub>	±8 (Note8)	mA	
		±4 (Note9)		
Operating temperature	T <sub>opr</sub>	-40~85	°C	
Input rise and fall time	dt/dv	0~10 (Note10)	ns/V	

Note4: Data retention only

Note5: Off-state

Note6: High or low state Note7:  $V_{CC} = 3.0 \sim 3.6 \text{ V}$ Note8:  $V_{CC} = 2.3 \sim 2.7 \text{ V}$ 

Note9:  $V_{CC} = 1.8 \text{ V}$ 

Note10:  $V_{IN} = 0.8 \sim 2.0 \text{ V}, V_{CC} = 3.0 \text{ V}$ 



### **Electrical Characteristics**

# DC Characteristics (Ta = -40~85°C, 2.7 V < V<sub>CC</sub> $\leq$ 3.6 V)

Characteristics		Symbol Test Condition			Min	Max	Unit	
		<b>G</b> ,ze.			V <sub>CC</sub> (V)		Max	Onic
Input voltage	High level	V <sub>IH</sub>		_	2.7~3.6	2.0	_	V
input voltage	Low level	V <sub>IL</sub>		_	2.7~3.6	_	0.8	٧
				$I_{OH} = -100 \mu A$	2.7~3.6	V <sub>CC</sub> - 0.2	_	
	High level	Voh	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	$I_{OH} = -6 \text{ mA}$	2.7	2.2	_	
				$I_{OH} = -8 \text{ mA}$	3.0	2.4	_	
Output voltage				$I_{OH} = -12 \text{ mA}$	3.0	2.2	_	V
		V <sub>OL</sub>	$V_{IN} = V_{IH}$ or $V_{IL}$	$I_{OL} = 100  \mu A$	2.7~3.6	_	0.2	
L Laurel	Low level			I <sub>OL</sub> = 6 mA	2.7	_	0.4	
	Low level			$I_{OL} = 8 \text{ mA}$	3.0	_	0.55	
				I <sub>OL</sub> = 12 mA	3.0	_	0.8	
Input leakage curre	ent	I <sub>IN</sub>	V <sub>IN</sub> = 0~3.6 V		2.7~3.6	_	±5.0	μΑ
3 state output off s	stata current	la-	$V_{IN} = V_{IH}$ or $V_{IL}$		2.7~3.6		140.0	
3-state output off-state current		loz	V <sub>OUT</sub> = 0~3.6 V		2.1~3.0		±10.0	μΑ
Power off leakage	current	I <sub>OFF</sub>	V <sub>IN</sub> , V <sub>OUT</sub> = 0~3.6 V		0	_	10.0	μΑ
		loo	V <sub>IN</sub> = V <sub>CC</sub> or GND		2.7~3.6	_	20.0	
Quiescent supply of	current	Icc	$V_{CC} \le (V_{IN}, V_{OUT}) \le 3.6 \text{ V}$		2.7~3.6	_	±20.0	μΑ
		Δl <sub>CC</sub>	$V_{IH} = V_{CC} - 0.6 V$ (pe	r input)	2.7~3.6	_	750	

# DC Characteristics (Ta = -40~85°C, 2.3 V $\leq$ V<sub>CC</sub> $\leq$ 2.7 V)

Characteristics		Symbol	Test Condition			Min	Max	Unit
					V <sub>CC</sub> (V)			
Input voltage	High level	V <sub>IH</sub>		_	2.3~2.7	1.6		V
input voltage	Low level	V <sub>IL</sub>		_	2.3~2.7	_	0.7	V
				$I_{OH} = -100 \ \mu A$	2.3~2.7	V <sub>CC</sub> - 0.2	_	
	High level	V <sub>OH</sub>	$V_{IN} = V_{IH}$ or $V_{IL}$	I <sub>OH</sub> = -4 mA	2.3	2.0	_	
				$I_{OH} = -6 \text{ mA}$	2.3	1.8	_	V
Output voltage				I <sub>OH</sub> = -8 mA	2.3	1.7	_	
		V <sub>OL</sub>	$V_{IN} = V_{IH}$ or $V_{IL}$	I <sub>OL</sub> = 100 μA	2.3~2.7	_	0.2	
	Low level			I <sub>OL</sub> = 6 mA	2.3	_	0.4	
				I <sub>OL</sub> = 8 mA	2.3	_	0.6	
Input leakage curre	nt	I <sub>IN</sub>	V <sub>IN</sub> = 0~3.6 V		2.3~2.7	_	±5.0	μА
2 state output off at	0		$V_{IN} = V_{IH}$ or $V_{IL}$ $V_{OUT} = 0 \sim 3.6 \text{ V}$		2.3~2.7	_	±10.0	μА
3-state output off-state current		loz			2.3~2.1		±10.0	
Power off leakage of	urrent	l <sub>OFF</sub>	V <sub>IN</sub> , V <sub>OUT</sub> = 0~3.6 V		0	_	10.0	μА
0			V <sub>IN</sub> = V <sub>CC</sub> or GND		2.3~2.7	_	20.0	
Quiescent supply cu	<u>-</u>	Icc	$V_{CC} \le (V_{IN}, V_{OUT}) \le 3.6 \text{ V}$		2.3~2.7	_	±20.0	μΑ



# DC Characteristics (Ta = $-40\sim85^{\circ}$ C, 1.8 V $\leq$ V<sub>CC</sub> < 2.3 V)

Character	stics	Symbol	Test Condition		V <sub>CC</sub> (V)	Min	Max	Unit
Input voltogo	High level	V <sub>IH</sub>			1.8~2.3	0.7 × V <sub>CC</sub>	_	V
Input voltage	Low level	V <sub>IL</sub>		_	1.8~2.3	_	0.2 × V <sub>CC</sub>	٧
	High level	V <sub>OH</sub>	$V_{IN} = V_{IH}$ or $V_{IL}$	$I_{OH} = -100 \mu A$	1.8	V <sub>CC</sub> - 0.2	_	
Output voltage				$I_{OH} = -4 \text{ mA}$	1.8	1.4	_	V
		V	$V_{IN} = V_{IH}$ or $V_{IL}$	I <sub>OL</sub> = 100 μA	1.8	_	0.2	
	Low level	V <sub>OL</sub>		I <sub>OL</sub> = 4 mA	1.8	_	0.3	
Input leakage curre	ent	I <sub>IN</sub>	V <sub>IN</sub> = 0~3.6 V		1.8	_	±5.0	μΑ
3-state output off-s	tate current	I <sub>OZ</sub>	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OUT} = 0 \sim 3.6 \text{ V}$		1.8	_	±10.0	μА
Power off leakage	current	I <sub>OFF</sub>	V <sub>IN</sub> , V <sub>OUT</sub> = 0~3.6 V		0	_	10.0	μΑ
Quioscont supply o	Quiescent supply current		$V_{IN} = V_{CC}$ or GND		1.8	_	20.0	μА
Quiescent supply o			$V_{CC} \le (V_{IN}, V_{OUT}) \le 3.6 \text{ V}$		1.8	_	±20.0	



# AC Characteristics (Ta = $-40 \sim 85$ °C, Input: $t_r = t_f = 2.0$ ns, $C_L = 30$ pF, $R_L = 500$ $\Omega$ )

Characteristics	Symbol	Symbol Test Condition		Min	Max	Unit
Characteristics	Symbol	rest Condition	V <sub>CC</sub> (V)	IVIIII	IVIAX	O I I
			1.8	100	_	MHz
Maximum clock frequency	f <sub>max</sub>	Figure 1, Figure 2	$2.5 \pm 0.2$	200	_	
			$3.3 \pm 0.3$	250	_	
	4		1.8	1.5	9.8	
Propagation delay time (CK-Q)	t <sub>pLH</sub>	Figure 1, Figure 2	$2.5 \pm 0.2$	8.0	6.2	ns
	t <sub>pHL</sub>		$3.3 \pm 0.3$	0.6	5.1	
			1.8	1.5	9.8	
3-state output enable time	t <sub>pZL</sub>	Figure 1, Figure 3	$2.5 \pm 0.2$	0.8	6.5	ns
	t <sub>pZH</sub>		$3.3 \pm 0.3$	0.6	5.0	
		Figure 1, Figure 3	1.8	1.5	7.7	ns
3-state output disable time	t <sub>pLZ</sub>		$2.5\pm0.2$	0.8	4.3	
			$3.3 \pm 0.3$	0.6	3.9	
	t <sub>w (H)</sub>	Figure 1, Figure 2	1.8	4.0		ns
Minimum pulse width (CK)			$2.5\pm0.2$	1.5	_	
			$3.3 \pm 0.3$	1.5	_	
			1.8	2.5	_	
Minimum set-up time	ts	Figure 1, Figure 2	$2.5 \pm 0.2$	1.5	_	ns
			$3.3 \pm 0.3$	1.5		<b> </b>
			1.8	1.0	_	
Minimum hold time	t <sub>h</sub>	Figure 1, Figure 2	$2.5 \pm 0.2$	1.0	_	ns
			$3.3 \pm 0.3$	1.0	_	
			1.8	_	0.5	
Output to output skew	t <sub>osLH</sub>	(Note11)	$2.5 \pm 0.2$	_	0.5	ns
	t <sub>osHL</sub>		$3.3 \pm 0.3$	_	0.5	

For  $C_L = 50$  pF, add approximately 300 ps to the AC maximum specification.

Note11: This parameter is guaranteed by design.

 $(t_{OSLH} = |t_{PLHm} - t_{PLHn}|, t_{OSHL} = |t_{PHLm} - t_{PHLn}|)$ 



# Dynamic Switching Characteristics (Ta = 25°C, Input: $t_r = t_f = 2.0$ ns, $C_L = 30$ pF)

Characteristics	Symbol	Test Condition			Тур.	Unit
Characteristics	Syllibol	rest Condition	V <sub>C</sub>	C (V)	τyp.	Offic
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (Note	12) 1	1.8	0.15	
Quiet output maximum dynamic V <sub>OL</sub>	V <sub>OLP</sub>	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (Note	12) 2	2.5	0.25	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (Note	12) 3	3.3	0.35	
	V <sub>OLV</sub>	$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (Note	12) 1	1.8	-0.15	٧
Quiet output minimum dynamic $V_{\mbox{OL}}$		$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (Note	12) 2	2.5	-0.25	
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (Note	12) 3	3.3	-0.35	
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (Note	12) 1	1.8	1.55	
Quiet output minimum dynamic V <sub>OH</sub>	V <sub>OHV</sub>	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (Note	12) 2	2.5	2.05	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (Note	12) 3	3.3	2.65	

Note12: This parameter is guaranteed by design.

#### **Capacitive Characteristics (Ta = 25°C)**

Characteristics	Symbol	Symbol Test Condition		Тур.	Unit
Characteristics	Syllibol	rest Condition	V <sub>CC</sub> (V)	τyp.	Offic
Input capacitance	C <sub>IN</sub>	_	1.8, 2.5, 3.3	6	pF
Output capacitance	Co	_	1.8, 2.5, 3.3	7	pF
Power dissipation capacitance	C <sub>PD</sub>	f <sub>IN</sub> = 10 MHz (Note1	3) 1.8, 2.5, 3.3	20	pF

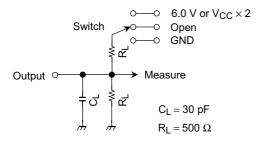
Note13: CPD is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8 \text{ (per bit)}$ 



#### **AC Test Circuit**



Parameter		Switch	
t <sub>pLH</sub> , t <sub>pHL</sub>	Open		
t <sub>pLZ</sub> , t <sub>pZL</sub>	6.0 V V <sub>CC</sub> × 2	$@V_{CC} = 3.3 \pm 0.3 \text{ V} \\ @V_{CC} = 2.5 \pm 0.2 \text{ V} \\ @V_{CC} = 1.8 \text{ V}$	
t <sub>pHZ</sub> , t <sub>pZH</sub>		GND	

Figure 1

#### **AC Waveform**

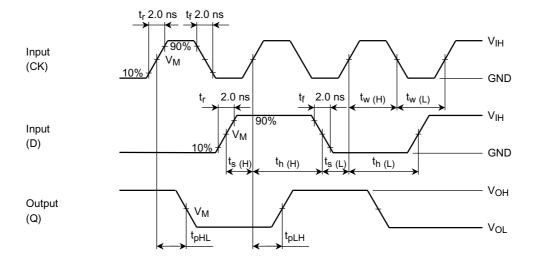


Figure 2  $t_{pLH}$ ,  $t_{pHL}$ ,  $t_{w}$ ,  $t_{s}$ ,  $t_{h}$ 

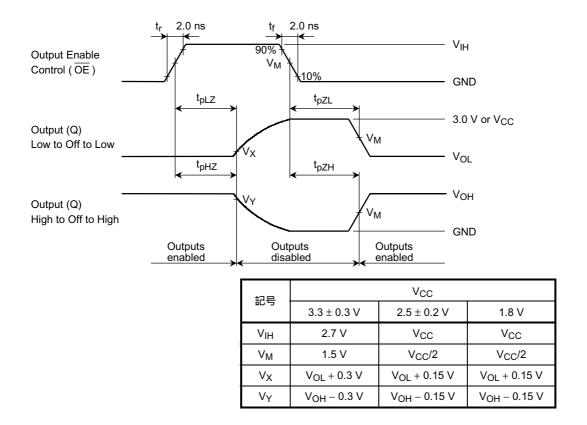
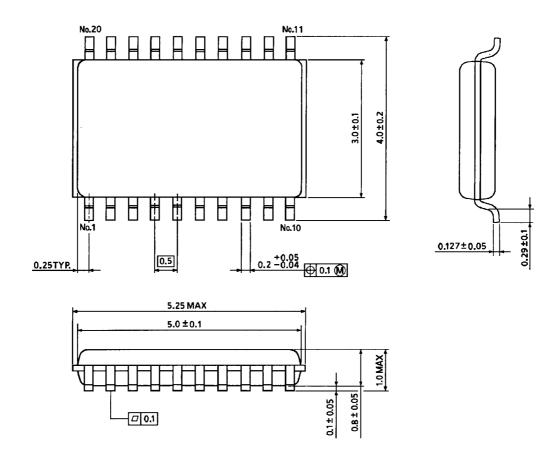


Figure 3  $t_{pLZ}$ ,  $t_{pHZ}$ ,  $t_{pZL}$ ,  $t_{pZH}$ 

# **Package Dimensions**



Weight: 0.03 g (typ.)